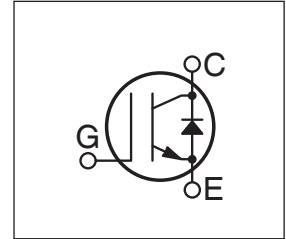
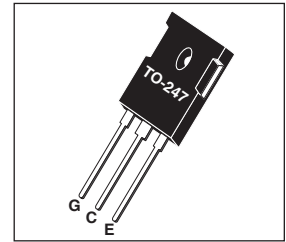


## POWER MOS 7® IGBT

The POWER MOS 7® IGBT is a new generation of high voltage power IGBTs. Using Punch Through Technology this IGBT is ideal for many high frequency, high voltage switching applications and has been optimized for high frequency switchmode power supplies.

- Low Conduction Loss
- Low Gate Charge
- Ultrafast Tail Current shutoff
- 100 kHz operation @ 800V, 11A
- 50 kHz operation @ 800V, 19A
- RBSOA Rated




### MAXIMUM RATINGS

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Parameter	APT25GP120BDQ1(G)	UNIT
$V_{CES}$	Collector-Emitter Voltage	1200	Volts
$V_{GE}$	Gate-Emitter Voltage	$\pm 30$	
$I_{C1}$	Continuous Collector Current @ $T_C = 25^\circ\text{C}$	69	Amps
$I_{C2}$	Continuous Collector Current @ $T_C = 110^\circ\text{C}$	33	
$I_{CM}$	Pulsed Collector Current <sup>①</sup> @ $T_C = 150^\circ\text{C}$	90	
RBSOA	Reverse Bias Safe Operating Area @ $T_j = 150^\circ\text{C}$	90A @ 960V	
$P_D$	Total Power Dissipation	417	Watts
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to 150	$^\circ\text{C}$
$T_L$	Max. Lead Temp. for Soldering: 0.063" from Case for 10 Sec.	300	

### STATIC ELECTRICAL CHARACTERISTICS

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	Units
$V_{(BR)CES}$	Collector-Emitter Breakdown Voltage ( $V_{GE} = 0V, I_C = 350\mu\text{A}$ )	1200			Volts
$V_{GE(TH)}$	Gate Threshold Voltage ( $V_{CE} = V_{GE}, I_C = 1\text{mA}, T_j = 25^\circ\text{C}$ )	3	4.5	6	
$V_{CE(ON)}$	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 25A, T_j = 25^\circ\text{C}$ )		3.3	3.9	
	Collector-Emitter On Voltage ( $V_{GE} = 15V, I_C = 25A, T_j = 125^\circ\text{C}$ )		3.0		
$I_{CES}$	Collector Cut-off Current ( $V_{CE} = 1200V, V_{GE} = 0V, T_j = 25^\circ\text{C}$ ) <sup>②</sup>			350	$\mu\text{A}$
	Collector Cut-off Current ( $V_{CE} = 1200V, V_{GE} = 0V, T_j = 125^\circ\text{C}$ ) <sup>②</sup>			3000	
$I_{GES}$	Gate-Emitter Leakage Current ( $V_{GE} = \pm 20V$ )			$\pm 100$	nA

 **CAUTION:** These Devices are Sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

## DYNAMIC CHARACTERISTICS

APT25GP120BDQ1(G)

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT	
$C_{ies}$	Input Capacitance	<b>Capacitance</b> $V_{GE} = 0V, V_{CE} = 25V$ $f = 1 \text{ MHz}$		2090		pF	
$C_{oes}$	Output Capacitance			200			
$C_{res}$	Reverse Transfer Capacitance			40			
$V_{GEP}$	Gate-to-Emitter Plateau Voltage	Gate Charge		7.5		V	
$Q_g$	Total Gate Charge <sup>(3)</sup>	$V_{GE} = 15V$		110		nC	
$Q_{ge}$	Gate-Emitter Charge	$V_{CE} = 600V$		15			
$Q_{gc}$	Gate-Collector ("Miller") Charge	$I_C = 25A$		50			
RBSOA	Reverse Bias Safe Operating Area	$T_J = 150^\circ C, R_G = 5\Omega, V_{GE} = 15V, L = 100\mu H, V_{CE} = 960V$	90			A	
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (25°C)</b> $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 25A$ $R_G = 5\Omega$ $T_J = +25^\circ C$		12		ns	
$t_r$	Current Rise Time			14			
$t_{d(off)}$	Turn-off Delay Time			70			
$t_f$	Current Fall Time			39			
$E_{on1}$	Turn-on Switching Energy <sup>(4)</sup>			500			μJ
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>(5)</sup>		1090				
$E_{off}$	Turn-off Switching Energy <sup>(6)</sup>		440				
$t_{d(on)}$	Turn-on Delay Time	<b>Inductive Switching (125°C)</b> $V_{CC} = 600V$ $V_{GE} = 15V$ $I_C = 25A$ $R_G = 5\Omega$ $T_J = +125^\circ C$		12		ns	
$t_r$	Current Rise Time			14			
$t_{d(off)}$	Turn-off Delay Time			110			
$t_f$	Current Fall Time			90			
$E_{on1}$	Turn-on Switching Energy <sup>(4)</sup>			500			μJ
$E_{on2}$	Turn-on Switching Energy (Diode) <sup>(5)</sup>			1575			
$E_{off}$	Turn-off Switching Energy <sup>(6)</sup>			1185			

## THERMAL AND MECHANICAL CHARACTERISTICS

Symbol	Characteristic	MIN	TYP	MAX	UNIT
$R_{\theta JC}$	Junction to Case (IGBT)			.30	°C/W
$R_{\theta JC}$	Junction to Case (DIODE)			1.18	
$W_T$	Package Weight		5.9		gm

① Repetitive Rating: Pulse width limited by maximum junction temperature.

② For Combi devices,  $I_{ces}$  includes both IGBT and FRED leakages

③ See MIL-STD-750 Method 3471.

④  $E_{on1}$  is the clamped inductive turn-on-energy of the IGBT only, without the effect of a commutating diode reverse recovery current adding to the IGBT turn-on loss. (See Figure 24.)

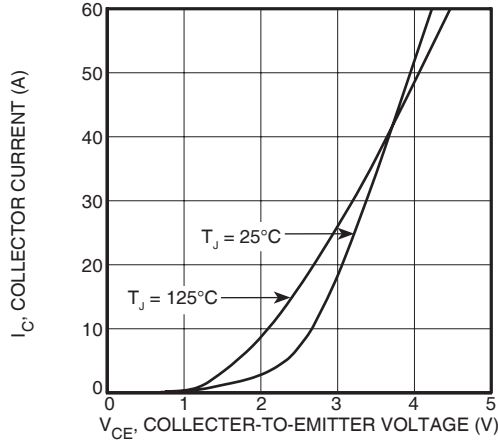
⑤  $E_{on2}$  is the clamped inductive turn-on energy that includes a commutating diode reverse recovery current in the IGBT turn-on switching loss. (See Figures 21, 22.)

⑥  $E_{off}$  is the clamped inductive turn-off energy measured in accordance with JEDEC standard JESD24-1. (See Figures 21, 23.)

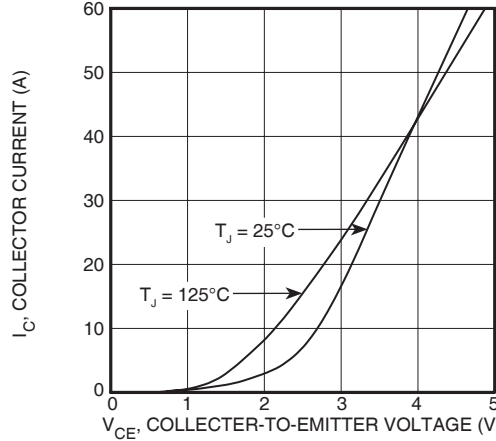
APT Reserves the right to change, without notice, the specifications and information contained herein.

**TYPICAL PERFORMANCE CURVES**

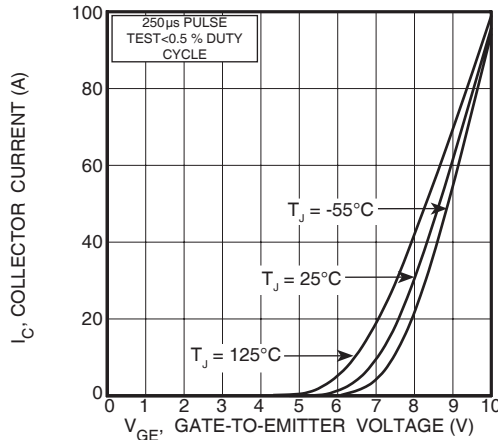
**APT25GP120BDQ1(G)**



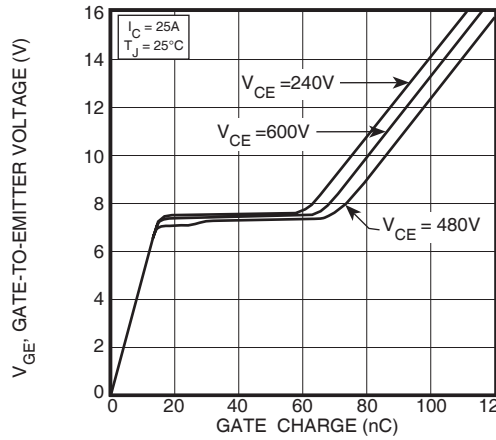
**FIGURE 1, Output Characteristics( $T_J = 25^\circ\text{C}$ )**



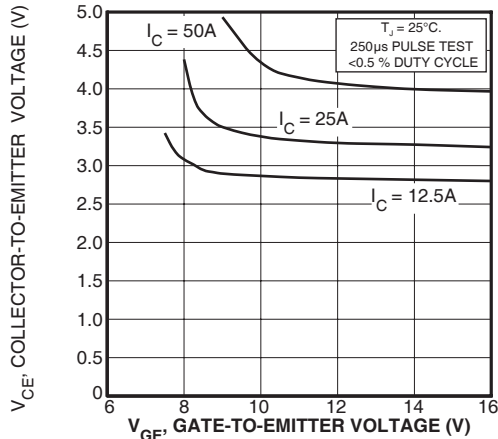
**FIGURE 2, Output Characteristics ( $T_J = 125^\circ\text{C}$ )**



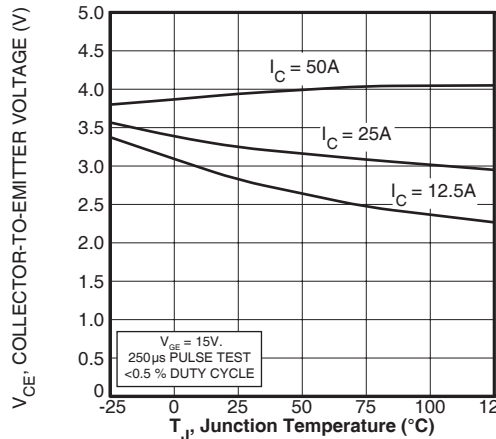
**FIGURE 3, Transfer Characteristics**



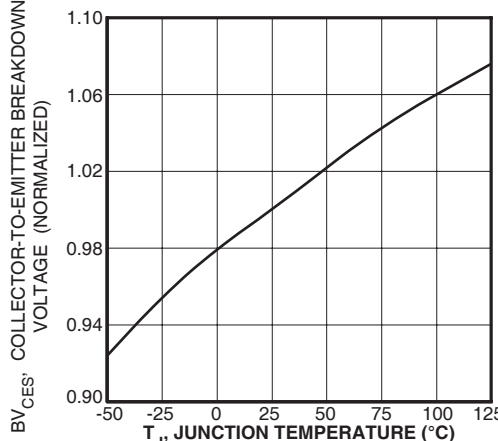
**FIGURE 4, Gate Charge**



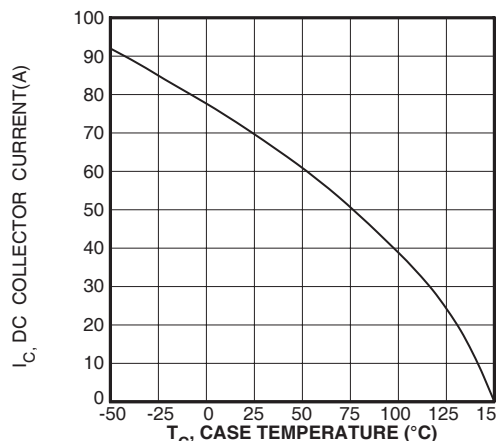
**FIGURE 5, On State Voltage vs Gate-to-Emitter Voltage**



**FIGURE 6, On State Voltage vs Junction Temperature**



**FIGURE 7, Breakdown Voltage vs. Junction Temperature**



**FIGURE 8, DC Collector Current vs Case Temperature**

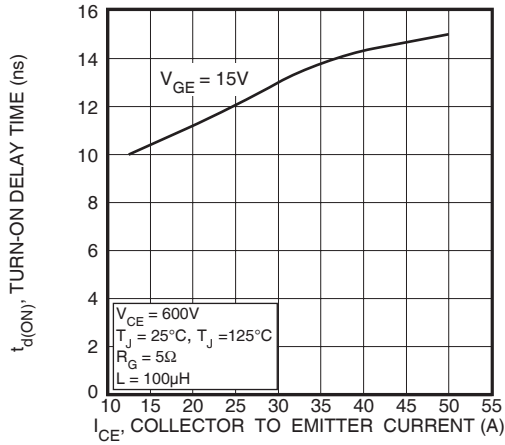


FIGURE 9, Turn-On Delay Time vs Collector Current

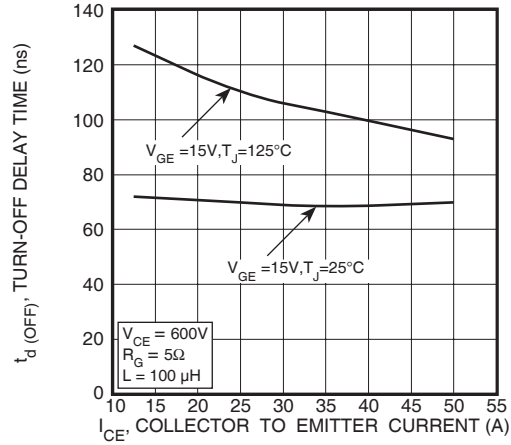


FIGURE 10, Turn-Off Delay Time vs Collector Current

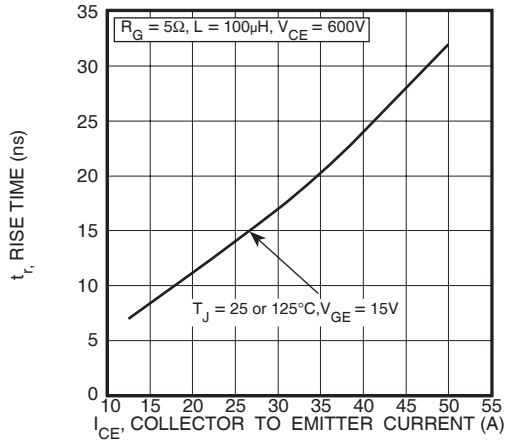


FIGURE 11, Current Rise Time vs Collector Current

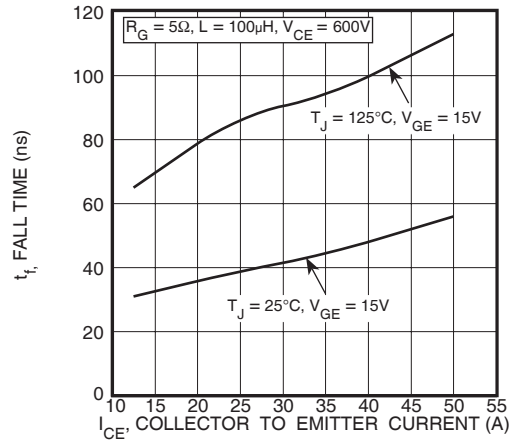


FIGURE 12, Current Fall Time vs Collector Current

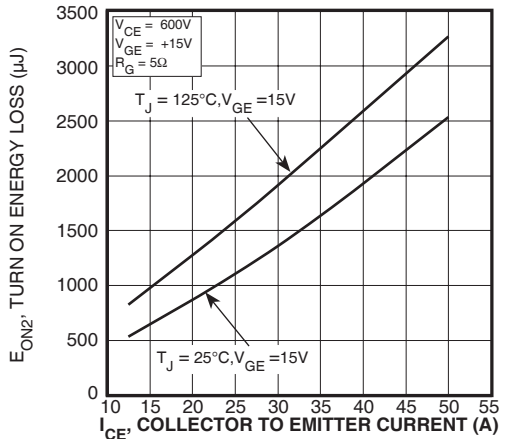


FIGURE 13, Turn-On Energy Loss vs Collector Current

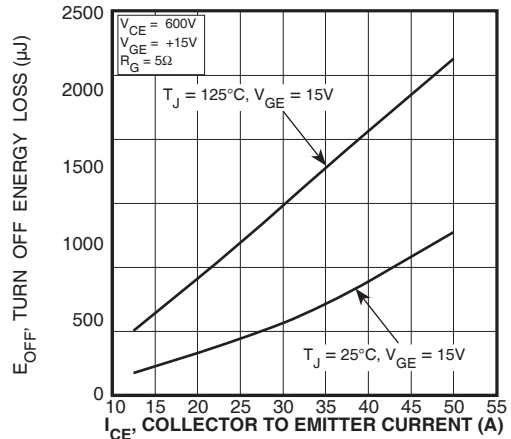


FIGURE 14, Turn Off Energy Loss vs Collector Current

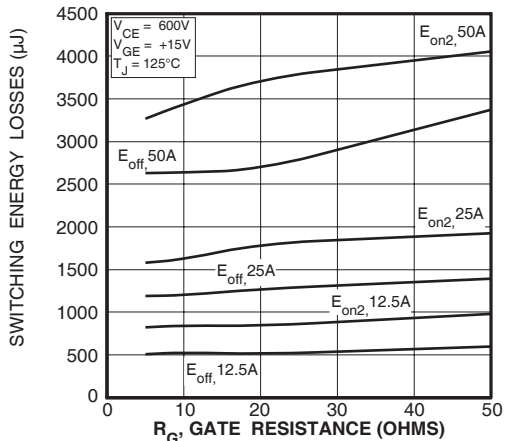


FIGURE 15, Switching Energy Losses vs. Gate Resistance

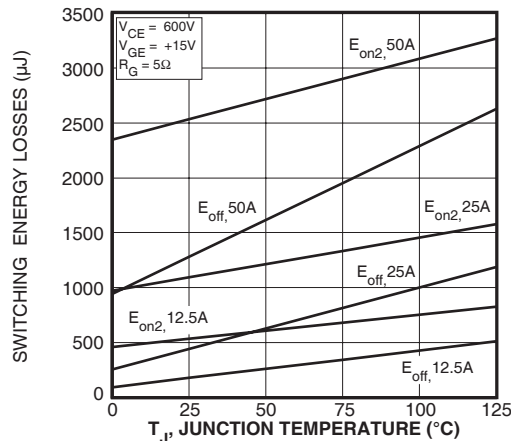


FIGURE 16, Switching Energy Losses vs Junction Temperature

# TYPICAL PERFORMANCE CURVES

# APT25GP120BDQ1(G)

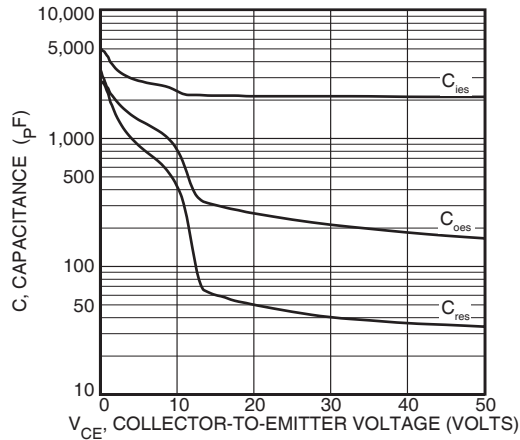


Figure 17, Capacitance vs Collector-To-Emitter Voltage

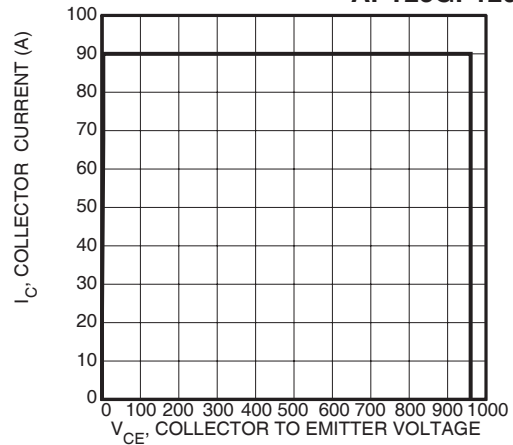


Figure 18, Minimum Switching Safe Operating Area

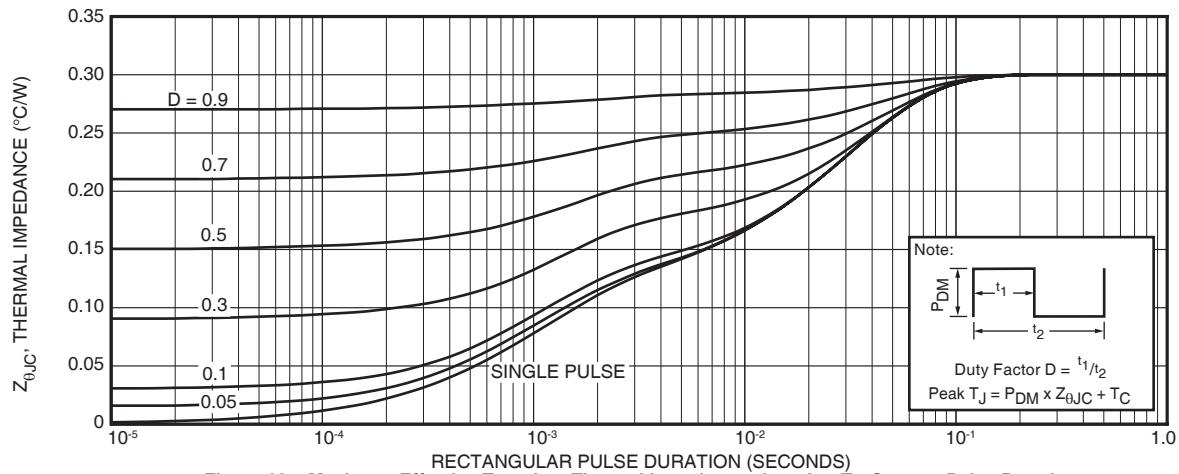


Figure 19a, Maximum Effective Transient Thermal Impedance, Junction-To-Case vs Pulse Duration

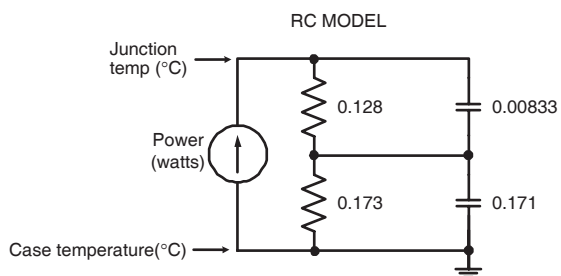


FIGURE 19b, TRANSIENT THERMAL IMPEDANCE MODEL

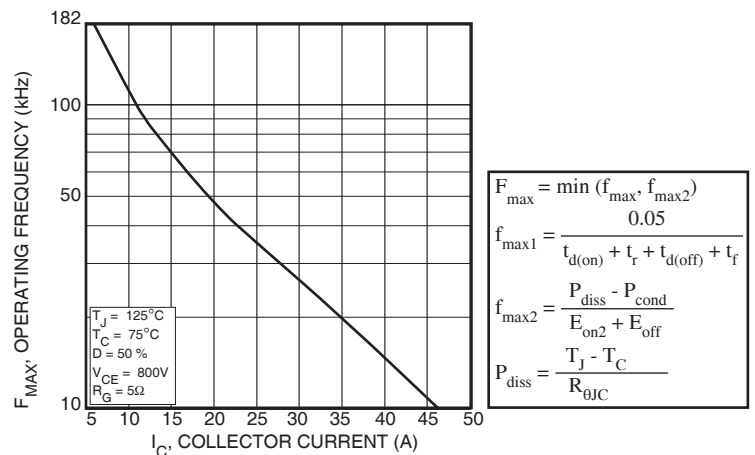


Figure 20, Operating Frequency vs Collector Current

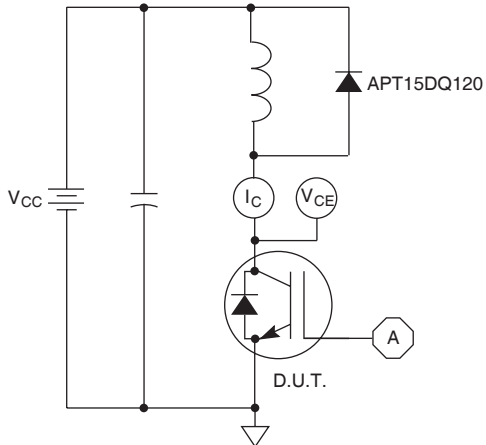


Figure 21, Inductive Switching Test Circuit

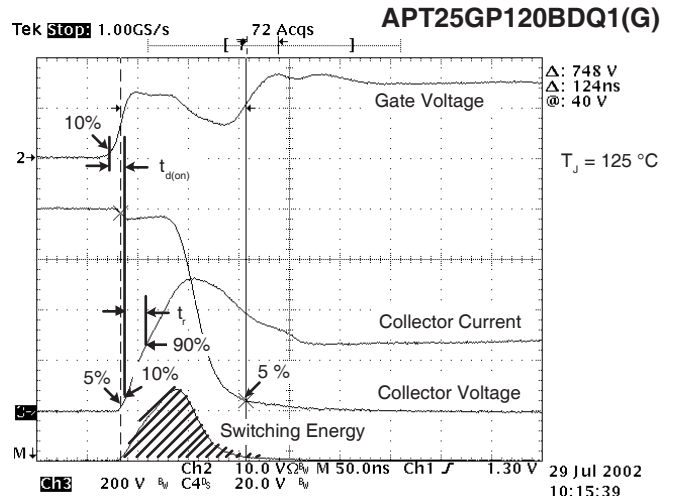


Figure 22, Turn-on Switching Waveforms and Definitions

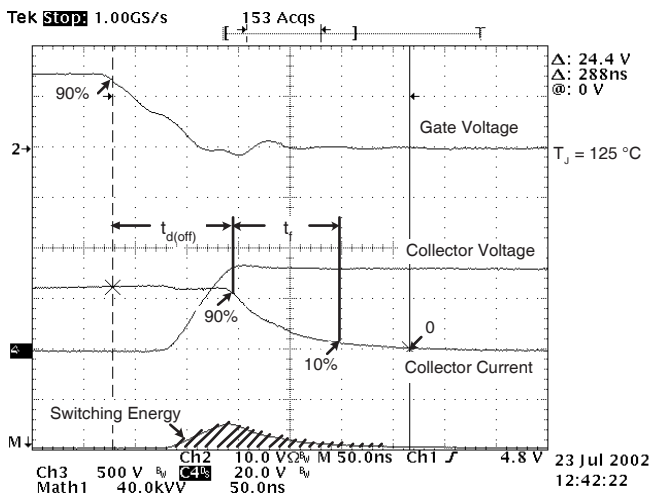


Figure 23, Turn-off Switching Waveforms and Definitions

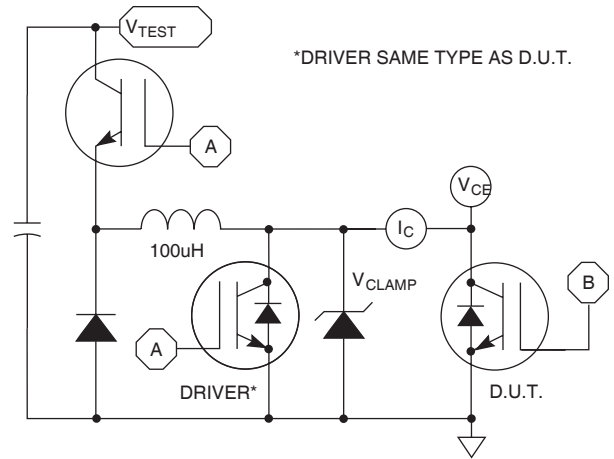


Figure 24,  $E_{ON1}$  Test Circuit

# ULTRAFAST SOFT RECOVERY ANTI-PARALLEL DIODE

**MAXIMUM RATINGS**

All Ratings:  $T_C = 25^\circ\text{C}$  unless otherwise specified.

Symbol	Characteristic / Test Conditions	APT25GP120BDQ1(G)		UNIT
$I_F(AV)$	Maximum Average Forward Current ( $T_C = 127^\circ\text{C}$ , Duty Cycle = 0.5)		15	Amps
$I_F(RMS)$	RMS Forward Current (Square wave, 50% duty)		29	
$I_{FSM}$	Non-Repetitive Forward Surge Current ( $T_J = 45^\circ\text{C}$ , 8.3ms)		110	

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Characteristic / Test Conditions	MIN	TYP	MAX	UNIT
$V_F$	Forward Voltage	$I_F = 25A$		3.24	Volts
		$I_F = 50A$		4.03	
		$I_F = 25A, T_J = 125^\circ\text{C}$		2.91	

**DYNAMIC CHARACTERISTICS**

Symbol	Characteristic	Test Conditions	MIN	TYP	MAX	UNIT
$t_{rr}$	Reverse Recovery Time	$I_F = 1A, di_F/dt = -100A/\mu s, V_R = 30V, T_J = 25^\circ\text{C}$	-	21		ns
$t_{rr}$	Reverse Recovery Time	$I_F = 15A, di_F/dt = -200A/\mu s, V_R = 800V, T_C = 25^\circ\text{C}$	-	240		
$Q_{rr}$	Reverse Recovery Charge		-	260		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	3	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 15A, di_F/dt = -200A/\mu s, V_R = 800V, T_C = 125^\circ\text{C}$	-	290		ns
$Q_{rr}$	Reverse Recovery Charge		-	960		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	6	-	Amps
$t_{rr}$	Reverse Recovery Time	$I_F = 15A, di_F/dt = -1000A/\mu s, V_R = 800V, T_C = 125^\circ\text{C}$	-	130		ns
$Q_{rr}$	Reverse Recovery Charge		-	1340		nC
$I_{RRM}$	Maximum Reverse Recovery Current		-	19		Amps

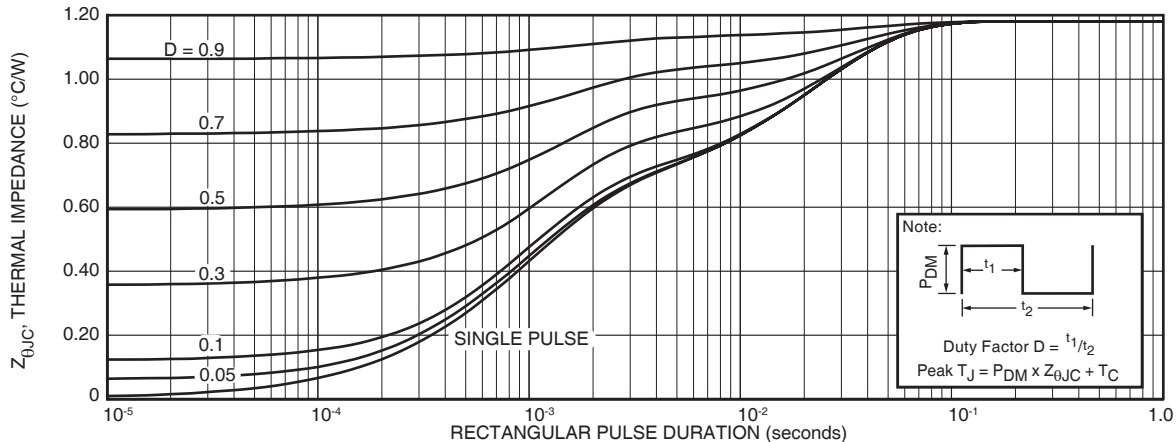


FIGURE 25a. MAXIMUM EFFECTIVE TRANSIENT THERMAL IMPEDANCE, JUNCTION-TO-CASE vs. PULSE DURATION

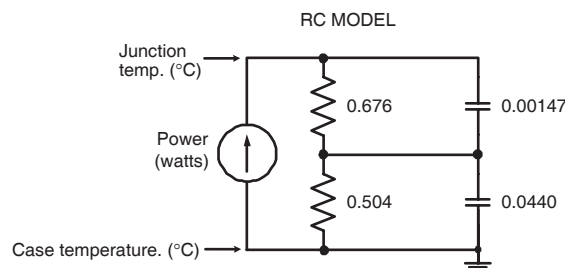


FIGURE 25b. TRANSIENT THERMAL IMPEDANCE MODEL

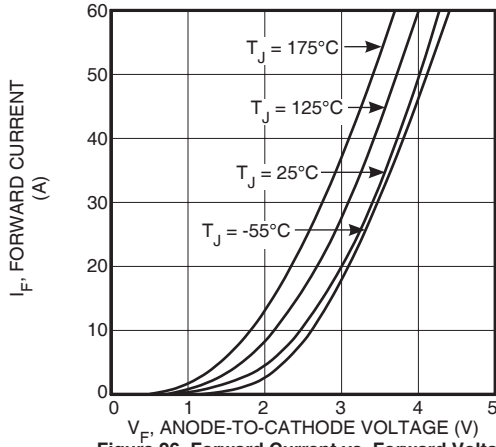


Figure 26. Forward Current vs. Forward Voltage

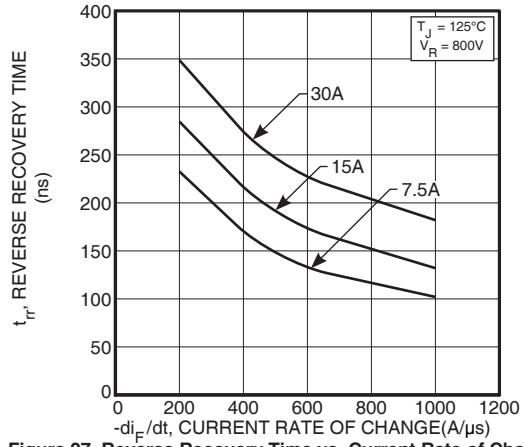


Figure 27. Reverse Recovery Time vs. Current Rate of Change

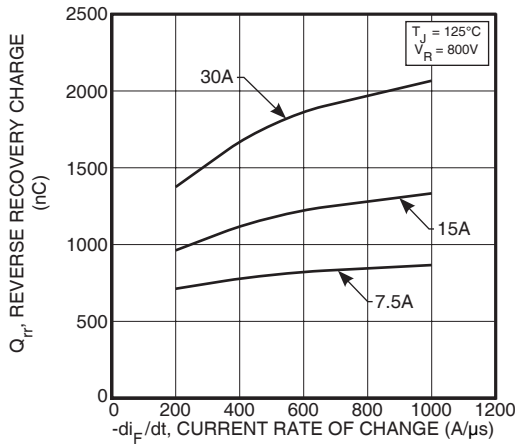


Figure 28. Reverse Recovery Charge vs. Current Rate of Change

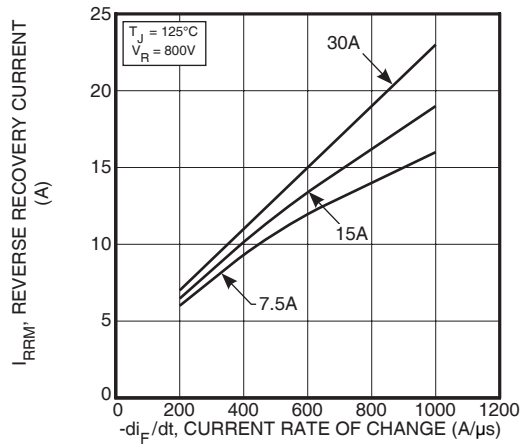


Figure 29. Reverse Recovery Current vs. Current Rate of Change

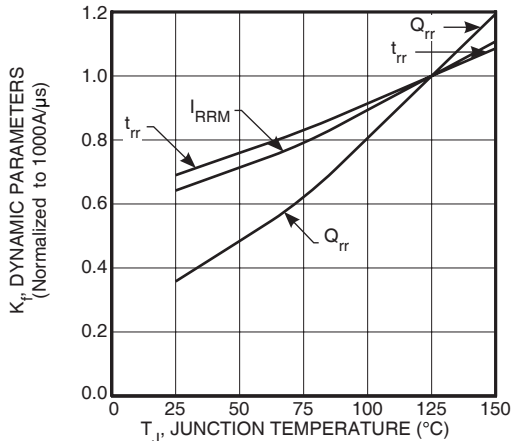


Figure 30. Dynamic Parameters vs. Junction Temperature

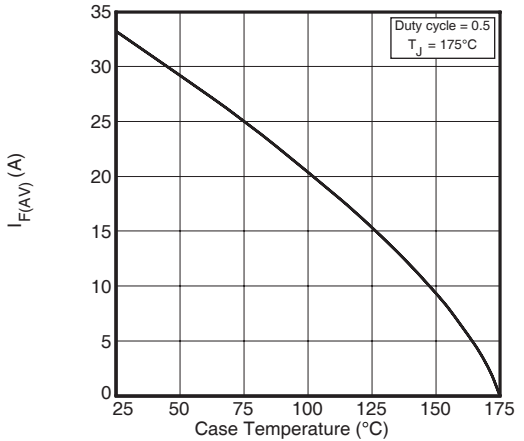


Figure 31. Maximum Average Forward Current vs. Case Temperature

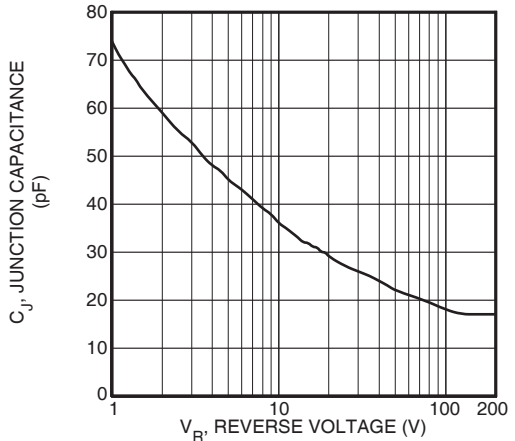


Figure 32. Junction Capacitance vs. Reverse Voltage



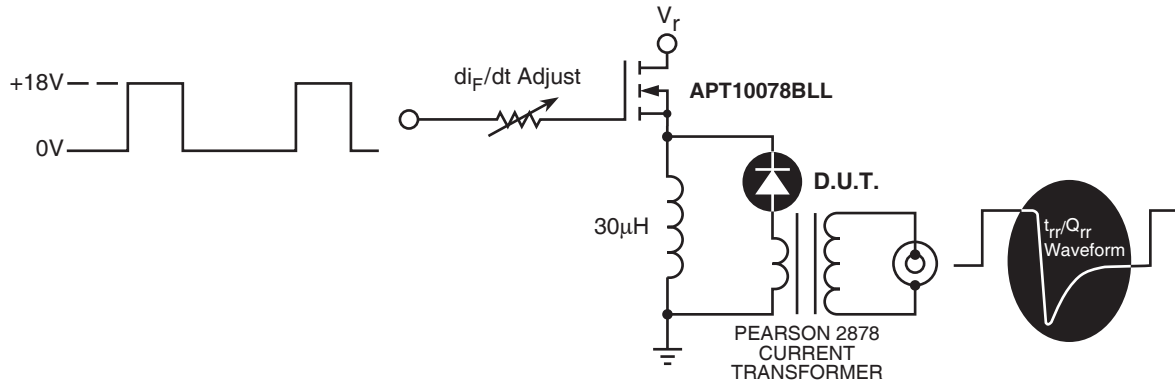


Figure 33. Diode Test Circuit

- 1  $I_F$  - Forward Conduction Current
- 2  $di_F/dt$  - Rate of Diode Current Change Through Zero Crossing.
- 3  $I_{RRM}$  - Maximum Reverse Recovery Current.
- 4  $t_{rr}$  - Reverse Recovery Time, measured from zero crossing where diode current goes from positive to negative, to the point at which the straight line through  $I_{RRM}$  and  $0.25 \cdot I_{RRM}$  passes through zero.
- 5  $Q_{rr}$  - Area Under the Curve Defined by  $I_{RRM}$  and  $t_{rr}$ .

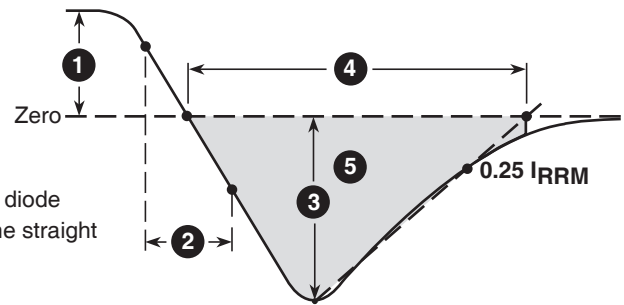
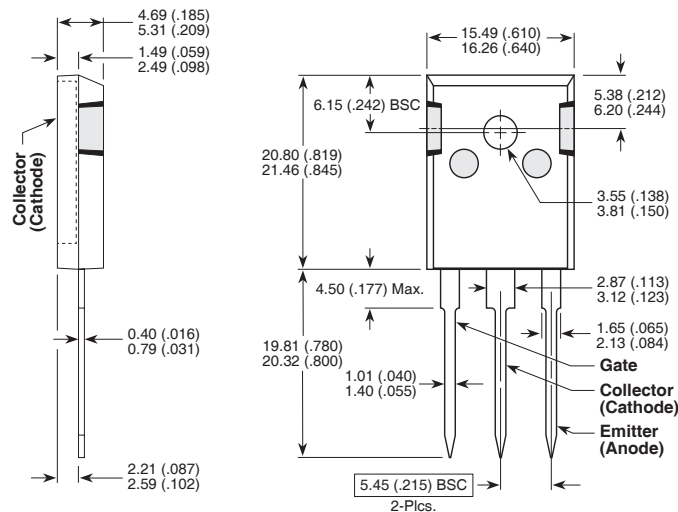


Figure 34. Diode Reverse Recovery Waveform and Definitions

TO-247 Package Outline

ⓔ1 SAC: Tin, Silver, Copper



Dimensions in Millimeters and (Inches)

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. US and Foreign patents pending. All Rights Reserved.

## Данный компонент на территории Российской Федерации

### Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

### Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: [info@moschip.ru](mailto:info@moschip.ru)

Skype отдела продаж:

moschip.ru

moschip.ru\_4

moschip.ru\_6

moschip.ru\_9